Temperature Dependence of SiO₂ Cathodoluminescence

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Outline

- Experimental set-up
- Theory and Results
 - Band theory of crystals
 - Electron excitation
 - One relaxation energy
 - Multiple relaxation energy's



- Qualitative temperature dependent model

Experimental Set-Up



Band Theory of (Crystalline) Conductors, Insulators and Semiconductors





Conductor Partially filled bands



Insulator Completely filled bands



Semiconductor Insulators at finite T



Momentum q

Cathodoluminescence of SiO₂ Mirror





Beam off

Beam on

Luminescence: Excitation and Relaxation



Effect of Beam Energy



Multi-Photon Luminescence





Multi-Photon Relaxation



Temperature Dependent Luminescence



-4 C

-80 C

-110 C

SLR Spectral Radiance vs Temperature



Temperature Dependent UV-Vis Spectra



Temperature Model for Multiphonon Luminescence



Low Temperature Model



High Temperature Model



Luminescence: Conclusions

Color of Electron-Induced Luminescence

	Gaussian Energy State			
nperature (K)		Blue	Red	
	0	$\rightarrow 0$	→max	
	Low	in between	in <mark>bet</mark> ween	
	High	\rightarrow half max	\rightarrow half max	
Ter				

Effective Fermi Level

Fermi Energy

- Identify specific defect mechanisms
- Quantify luminescence intensities, peak positions, and peak shifts with T
- Study initial time dependence as traps fill to E_f^{eff}
- Make lower T (<30 K) and higher (<400 K) T measurements

Future Work



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